VHF QUADRATURE MODULATOR

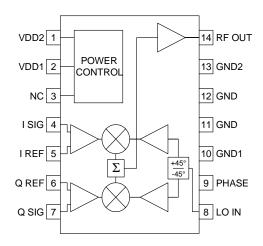
- Digital and Spread-Spectrum Systems
- GMSK, QPSK, DQPSK, QAM Modulation
- Private Mobile Radio and TETRA systems
- AM, SSB, DSB Modulation
- Image-Reject Upconverters

Product Description

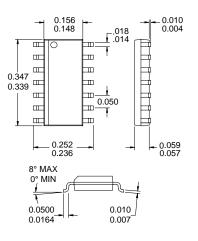
The RF2485 is a monolithic integrated universal modulation system capable of generating modulated AM, PM, or compound carriers in the VHF and UHF frequency range. The IC contains all of the required components to implement the modulation function including differential amplifiers for the baseband inputs, a 90° hybrid phase splitter, limiting LO amplifiers, two balanced mixers, a combining amplifier, and an output RF amplifier which will drive a 50Ω load. Component matching, which can only be accomplished with monolithic construction, is used to full advantage to obtain excellent amplitude balance and high phase accuracy. The unit features low power consumption, single power supply operation and adjustment free operation with no external parts required to operate the part as specified.

Optimum Technology Matching® Applied

Si BJT ☐ GaAs HBT **▼** GaAs MESFET ☐ Si Bi-CMOS ☐ SiGe HBT ☐ Si CMOS



Functional Block Diagram



Package Style: SOIC-14

Features

- Single 5V Power Supply
- Low Power
- Excellent Amplitude and Phase Balance
- Extremely Low Broadband Noise Floor
- 200 MHz to 600 MHz Operation

Ordering Information

RF2485 VHF Quadrature Modulator RF2485 PCBA Fully Assembled Evaluation Board

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MODULATORS AND UPCONVERTERS

Absolute Maximum Ratings

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Parameter	Rating	Unit				
Supply Voltage	-0.5 to +7.5	V_{DC}				
Input LO and RF Levels	+10	dBm				
Operating Ambient Temperature	-40 to +85	°C				
Storage Temperature	-40 to +150	°C				



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Parameter	;	Specification	1	Unit	Condition
Farailletei	Min.	Тур.	Max.	Oilit	Condition
LO Input					T=25°C, V _{DD} =5V _{DC} , I&Q inputs=2V _{PP}
Frequency Range	200		600	MHz	
Power Level	-3		+6	dBm	
Input VSWR		1.2:1			With external 50Ω termination; see applica-
Modulation Input					tion schematic, note A.
Frequency Range	DC		100	MHz	
Reference Voltage (V _{REF})	2.0		3.0	V	
Modulation (I&Q)		V _{REF} ±0.7		V	I & Q signals for -0.5dBm output power.
Modulation (I&Q)		V _{REF} ±1.5		V	I & Q signals for +5dBm output power.
Maximum Modulation (I&Q)		V _{REF} ±2.5		V	In-phase and quadrature signals.
Input Resistance		3000		Ω	in pridoc and quadratare digitals.
DC Offset		50	150	mV	I _{SIG} -I _{REF} and Q _{SIG} -Q _{REF} ; to achieve maxi-
					mum carrier suppression.
Amplitude Error (I/Q)		0.2		dB	
Quadrature Phase Error		±1	±3	٥	From 350MHz to 450MHz.
RF Output					V _{DD} =5V, LO Power=0dBm, LO
iti Gutput					Freq=400MHz, SSB, I&Q input=0.7V _P
Output Power	-1.5	-0.5		dBm	
Output Impedance		50		Ω	
Output VSWR		1.5:1	4.47	dDay/Ll-	At CMI In affect
Broadband Noise Floor Sideband Suppression	30	-149 43	-147	dBm/Hz dB	At 5MHz offset Unadjusted
Carrier Suppression	20	26		dВ	Modulation DC offset can be externally
Carrier Suppression	20	20		dB	adjusted for optimum suppression. Suppres-
					sion is typically better than 25dB without
					adjustment.
IM3	-40	-52		dBc	
TETRA Modulation	2.0	0.5	0.0	al Duna	4.7\/ TETDA Madulation
Channel Power	-3.0	-2.5	-2.0	dBm	1.7V _{P-P} TETRA Modulation LO, 450MHz @ -5.0dBm, V _{REF} 2.5V
Adjacent Channel Power				dBc	VCC=5.0V
Rejection				UDC	VCC=5.0 V
25kHz	-47.0	-48.0	-49.0	dBc	
50kHz	-67.0	-68.5	-70.0	dBc	
Power Supply					
Voltage		5		V	Specifications
	4.5	_	5.5	V	Operating Limits
Current		28	39	mA	Operating

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Preliminary RF2485

Pin	Function	Description	Interface Schematic
1	VDD2	Power supply for the RF Output amplifier. An external RF bypass capacitor is needed. The trace length between the pin and the bypass capacitor should be minimized. The ground side of the capacitor should connect immediately to the ground plane.	
2	VDD1	Power supply for all other circuits. An external RF bypass capacitor is needed.	
3	NC	No connection.	
4	I SIG	Baseband input to the I mixer. This pin is DC coupled. Maximum output power is obtained when the input signal has a peak to peak amplitude of 5 V. The DC level supplied to this pin should be 2.5±0.5 V. The SIG and REF inputs are inputs of a differential amplifier. Therefore the REF and SIG inputs are interchangeable. If swapping the I SIG and I REF pins, the Q SIG and Q REF also need to be swapped to maintain the correct phase. It is also possible to drive the SIG and REF inputs in a balanced mode. This will increase the gain.	I REF I SIG
5	I REF	Reference voltage for the I mixer. This voltage should be the same as the DC voltage supplied to the I SIG pin. To obtain a carrier suppression of better than 40dB it may be tuned ±0.15V (relative to the I SIG DC voltage). Without tuning, it will typically be better than 25dB.	See pin 4.
6	Q REF	Reference voltage for the Q mixer. This voltage should be the same as the DC voltage supplied to the Q SIG pin. To obtain a carrier suppression of better than 40dB it may be tuned ±0.15V (relative to the Q SIG DC voltage). Without tuning, it will typically be better than 25dB. The SIG and REF inputs are inputs of a differential amplifier. Therefore the REF and SIG inputs are interchangeable. If swapping the I SIG and I REF pins, Q SIG and Q REF also need to be swapped to maintain correct phase. It is also possible to drive the SIG and REF inputs in a balanced mode. This will increase the gain.	Same as pin 3.
7	Q SIG	Baseband input to the Q mixer. This pin is DC coupled. Maximum output power is obtained when the input signal has a peak to peak amplitude of 5V. The DC level supplied to this pin should be 2.5 ± 0.5 V.	Same as pin 4.
8	LO IN	The input of the phase shifting network. This high impedance input can be matched with an external 56Ω termination resistor. This pin is internally connected to ground through a $4k\Omega$ resistor. Putting a DC voltage on this pin is not recommended. However, connecting this pin to ground, e.g., through a shunt inductor, is allowed.	LO INO
9	PHASE	This pin allows to adjust the phase of the I/Q signals. However, the control is very sensitive and hard to control. Control voltage change for a few degrees adjustment is in the order of 10 mV. Device to device and temperature variation are not characterized. Therefore it is not recommended to use this pin; leave it not connected. Do NOT connect to ground.For compensating large errors in the I/Q signals supplied to the device or in control loops this pin may prove useful.	PHASE
10	GND1	Ground connection of the LO phase shift network. This pin should be connected directly to the ground plane.	
11	GND	Ground connection for other circuits. Keep traces short and connect to ground plane immediately.	
12	GND	Same as pin 11.	
13	GND2	Ground connection for the RF output stage. A good ground connection is especially important at this pin to avoid interference with other circuits.	

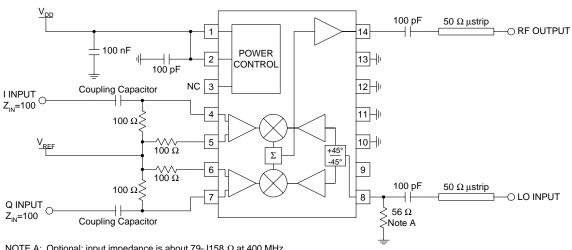
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RF2485 Preliminary

Pin	Function	Description	Interface Schematic
14	RF OUT	50Ω output. This pin carries a DC voltage, and an external blocking capacitor is recommended.	RF OUT

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Application Schematic

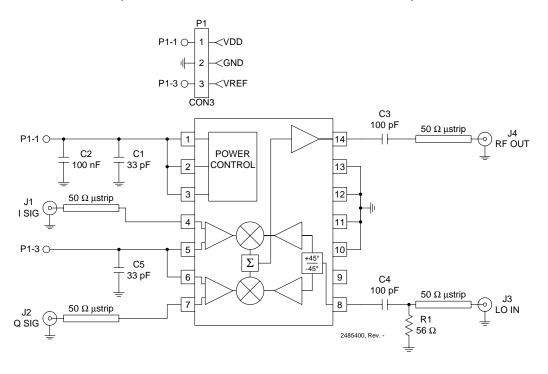


NOTE A: Optional; input impedance is about 79-J158 Ω at 400 MHz without resistor. SMD resistor mounted adjacent to package pin, grounded through a via to the ground plane.

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Evaluation Board Schematic

(Download Bill of Materials from www.rfmd.com.)

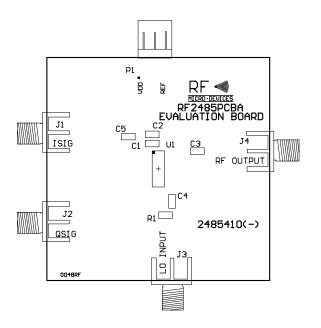


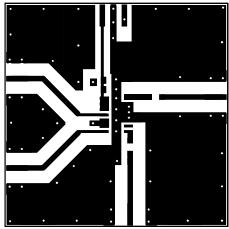
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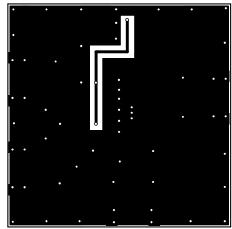
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Evaluation Board Layout Board Size 2.0" x 2.0"

Board Thickness 0.031", Board Material FR-4







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